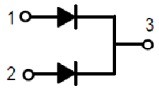
Silicon Schottky Diode, 400A

Features

- Guard Ring Protection
- Low forward voltage drop
- High surge current capability
- Up to 100V V_{RRM}





TWIN TOWER PACKAGE

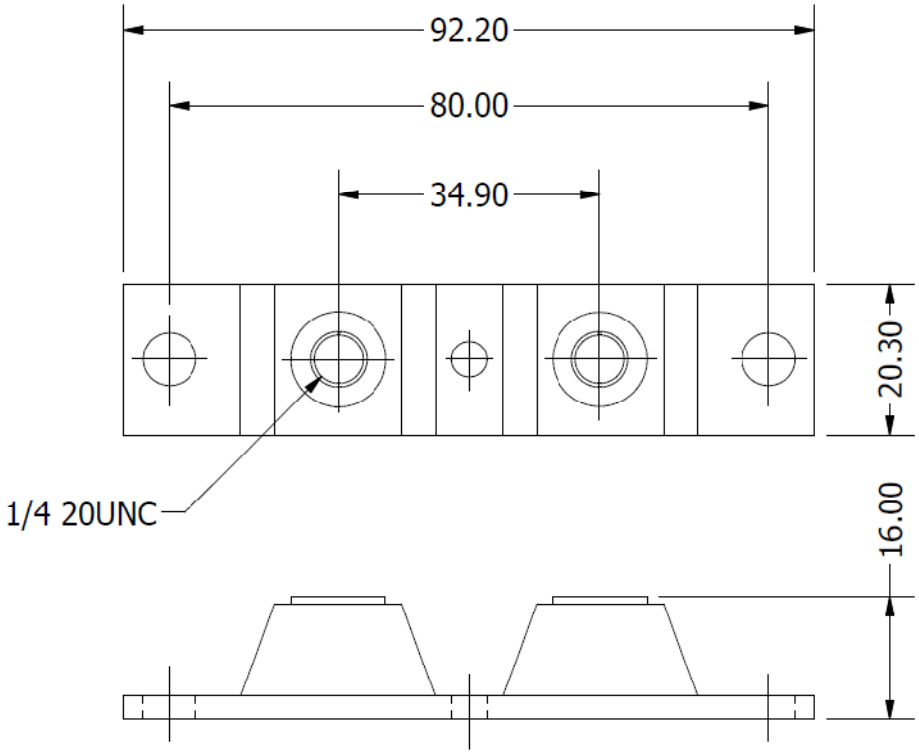
Maximum Ratings (T_J = 25°C unless otherwise specified)							
Parameter	**Symbol**	**Conditions**	**MBR40045CT (R)**	**MBR40060CT (R)**	**MBR40080CT (R)**	**MBR400100CT(R)**	**Units**
Repetitive peak reverse voltage	V_{RRM}		45	60	80	100	V
RMS reverse voltage	V_{RMS}		32	42	56	70	V
DC blocking voltage	V_{DC}		45	60	80	100	V
Average forward current	$I_{F(AV)}$	$T_C \leq 125$ °C	400	400	400	400	A
Non-repetitive forward surge current, half sine-wave	I_{FSM}	T_C = 25 °C t_p = 8.3 ms	3000	3000	3000	3000	A

Electrical Characteristics (T_J = 25°C unless otherwise specified)							
Parameter	**Symbol**	**Conditions**	**MBR40045CT (R)**	**MBR40060CT (R)**	**MBR40080CT (R)**	**MBR400100CT(R)**	**Units**
DC forward voltage	V_F	I_F = 200 A T_J = 25 °C	0.68	0.68	0.68	0.68	V
DC reverse current	I_R	V_R = 20 V T_J = 25 °C	5	5	5	5	mA
		V_R = 20 V T_J = 125°C	200	200	200	200	

Thermal Characteristics (T_J = 25°C unless otherwise specified)							
Parameter	**Symbol**		**MBR40045CT (R)**	**MBR40060CT (R)**	**MBR40080CT (R)**	**MBR400100CT(R)**	**Units**
Thermal resistance junction to case	R_{thJ-C}		0.35	0.35	0.35	0.35	°C/W
Operating, storage temperature range	T_J , T_{stg}		- 40 to +175	- 40 to +175	- 40 to +175	- 40 to +175	°C

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Package Outline



ALL DIMENSIONS IN MM

Ordering Table

MBR	*400*	*45*	*CT*
1	2	3	4

1 – Device Type
- MBR = Schottky Barrier Diode Module

2 – Current Rating = $I_{F(AV)}$

3 – Voltage = V_{RRM}

4 – Polarity
- CT = Normal (Cathode to Base)
- CTR = Reverse (Anode to Base)

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